

OM SENI

SM05T1G Series

ESD Protection Diode Array

Dual Common Anode

These dual monolithic silicon surge protection diodes are designed for applications requiring transient overvoltage protection capability. They are intended for use in voltage and ESD sensitive equipment such as computers, printers, business machines, communication systems, medical equipment and other applications. Their dual junction common anode design protects two separate lines using only one package. These devices are ideal for situations where board space is at a premium.

Specification Features:

- SOT-23 Package Allows Either Two Separate Unidirectional Configurations or a Single Bidirectional Configuration
- Working Peak Reverse Voltage Range – 5.0 V to 36 V
- Peak Power – 300 Watt (8/20 μ s)
- Low Leakage – 1.0 μ A
- These are Pb-Free Devices

Mechanical Characteristics:

CASE: Void-Free, Transfer-Molded, Thermosetting Plastic Case

FINISH: Corrosion Resistant Finish, Easily Solderable

MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES:

260°C for 10 Seconds

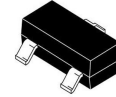
Package Designed for Optimal Automated Board Assembly

Small Package Size for High Density Applications

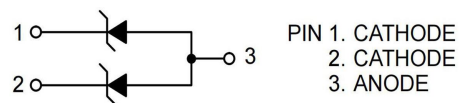
Available in 8 mm Tape and Reel

Use the Device Number to Order the 7 Inch/3,000 Unit Reel

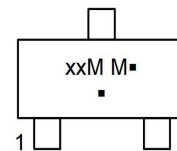
Replace the “T1” with “T3” in the Device Number to Order the 13 Inch/10,000 Unit Reel



SOT-23
CASE 318
STYLE 12



MARKING DIAGRAM



xxM = Device Code
xx = 05, 12, 15, 24, 36
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
SM05T1G	SOT-23 (Pb-Free)	3,000/Tape & Reel
SM12T1G	SOT-23 (Pb-Free)	3,000/Tape & Reel
SM15T1G	SOT-23 (Pb-Free)	3,000/Tape & Reel
SM24T1G	SOT-23 (Pb-Free)	3,000/Tape & Reel
SM36T1G	SOT-23 (Pb-Free)	3,000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Power Dissipation @ 20 μ s (Note 1) @ $T_L \leq 25^\circ\text{C}$	P_{pk}	300	W
IEC 61000-4-2 (ESD) Air Contact		± 15 ± 26	kV
IEC 61000-4-4 (EFT)		40	A
IEC 61000-4-5 (Lightning)		12	A
Total Power Dissipation on FR-5 Board (Note 2) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	1.8 556	$\text{mW}/^\circ\text{C}$ $^\circ\text{C}/\text{W}$
Total Power Dissipation on Alumina Substrate (Note 3) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	2.4 417	$\text{mW}/^\circ\text{C}$ $^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to +150	$^\circ\text{C}$
Lead Solder Temperature – Maximum (10 Second Duration)	T_L	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

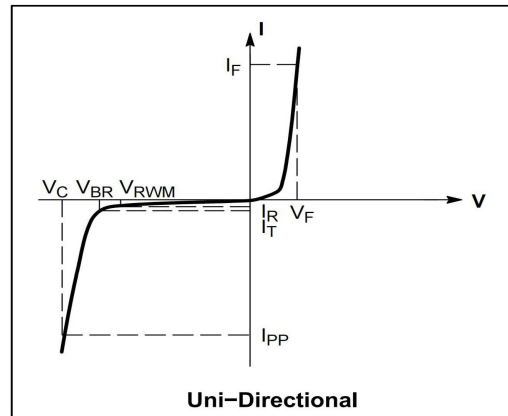
1. Non-repetitive current pulse per Figure 3
2. FR-5 = 1.0 x 0.75 x 0.62 in.
3. Alumina = 0.4 x 0.3 x 0.024 in., 99.5% alumina

NOTE: Other voltages may be available upon request

ELECTRICAL CHARACTERISTICS

UNIDIRECTIONAL (Circuit tied to Pins 1 and 3 or 2 and 3)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
ΘV_{BR}	Maximum Temperature Coefficient of V_{BR}
I_F	Forward Current
V_F	Forward Voltage @ I_F
Z_{ZT}	Maximum Zener Impedance @ I_{ZT}
I_{ZK}	Reverse Current
Z_{ZK}	Maximum Zener Impedance @ I_{ZK}



ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Device*	Device Marking	V _{RWM}	I _R @ V _{RWM}	V _{BR} , Breakdown Voltage		I _T	V _C @ I _{PP} = 1 Amp	Max I _{PP} (Note 4)	Typical Capacitance
				(Volts)					(pF)
		(Volts)	(μA)	Min	Max	mA	(Volts)	(Amps)	Pin 1 to 3 @ 0 Volts
SM05T1G	05M	5	10	6.2	7.3	1.0	9.8	17	225
SM12T1G	12M	12	1.0	13.3	15.75	1.0	19	12	95
SM15T1G	15M	15	1.0	16.7	19.6	1.0	24	10	100
SM24T1G	24M	24	1.0	26.7	31.35	1.0	43	5.0	60
SM36T1G	36M	36	1.0	40.0	46.95	1.0	60	4.0	45

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TYPICAL CHARACTERISTICS

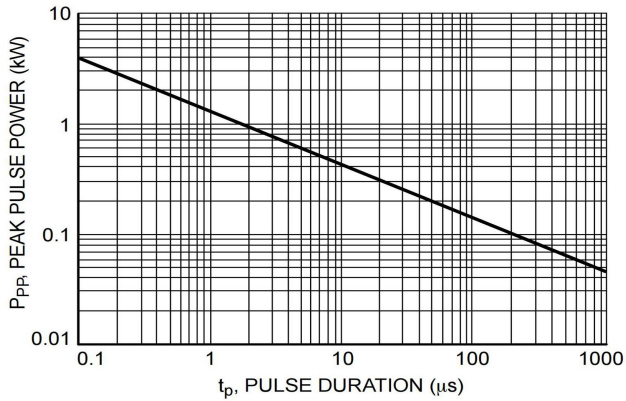


Figure 1. Non-Repetitive Peak Pulse Power versus Pulse Time

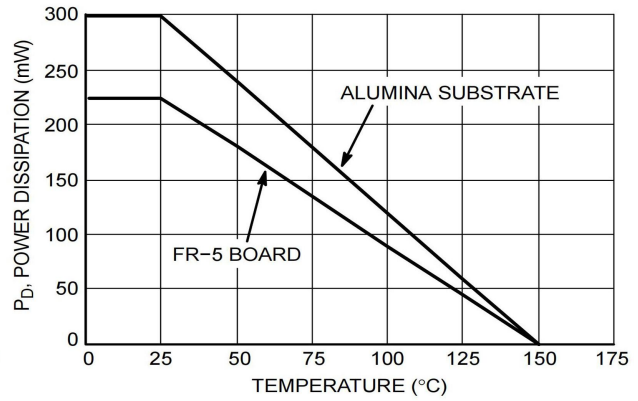


Figure 2. Steady State Power Derating Curve

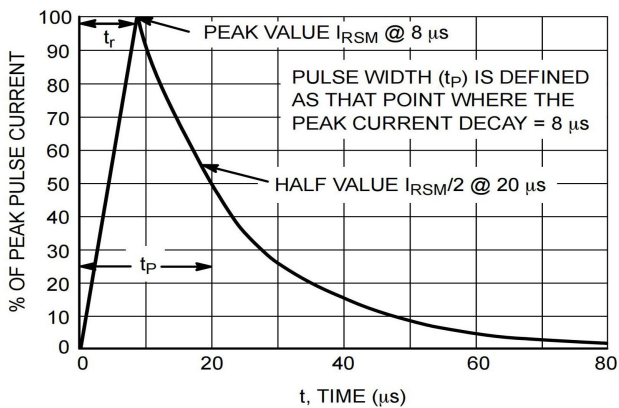


Figure 3. 8/20 μ s Pulse Waveform

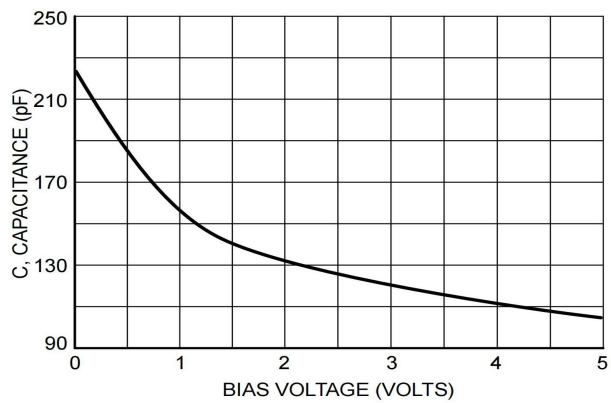


Figure 4. Typical Diode Capacitance (SM05)

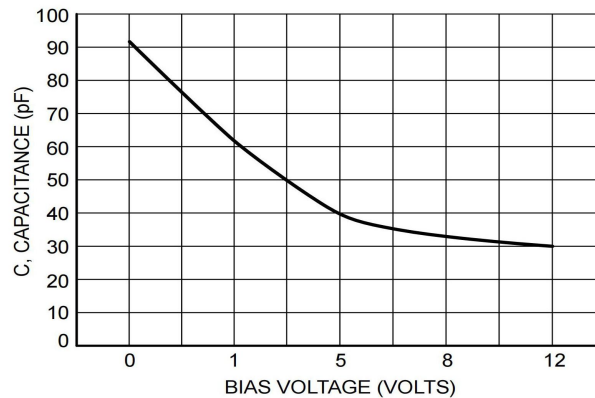


Figure 5. Typical Diode Capacitance (SM12)